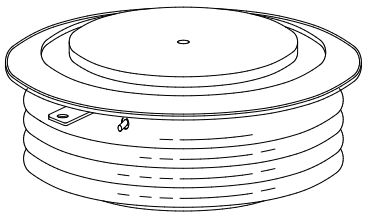
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T17D



Device Type	V_{RRM} (1)	V_{DRM} (1)	V_{RSM} (1)
KP3600/46	4000	4000	4600
KP3600/48	4200	4200	4800
KP3600/50	4400	4400	5000
KP3600/52	4600	4600	5200

V_{RRM} = Repetitive peak reverse voltage
V_{DRM} = Repetitive peak off state voltage
V_{RSM} = Non repetitive peak reverse voltage (2)

Notes:
(1) All voltage ratings are specified for an applied 50Hz sinusoidal waveform over the temperature range -40 °C to +125 °C.
(2) 10 msec. max. pulse width
(3) Maximum value for Tj = 125 °C.
(4) Minimum value for linear and exponential waveshape to 67% rated V_{DRM}. Gate open. Tj = 125 °C.
(5).The value of di/dt is established in accordance with EIA/NIMA Standard JB/T 8950.2-2013

Repetitive peak reverse leakage and off state leakage	I_{RRM}/I_{DRM}	5 mA 250 mA (3)
Critical rate of voltage rise	dv/dt (4)	2000 V/μ

Average value of on-state current	$I_{T(AV)}$	3600	A	Sinewave,180° conduction,T_c=70°C
RMS value of on-state current	I_{TRMS}	5652	A	Nominal value
Peak one cycle surge (non repetitive) current	I_{TSM}	60000	A	10.0 msec (50Hz), sinusoidal wave-shape, 180° conduction, T_j = 125 °C
I square t	I^2t	$1.8x10^7$	A^2s	10 msec

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